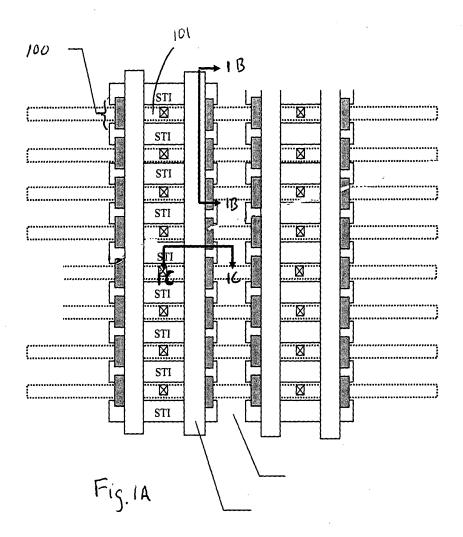
Docket No. N1085-00125 Inventors: Chia-Ta Hsieh et al. "Flash Memory Cell Having Multi-Program Channels" Sheet 1 of 8



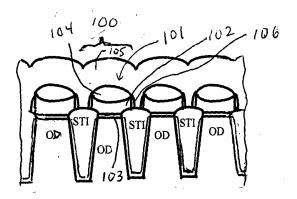


Fig. 1B

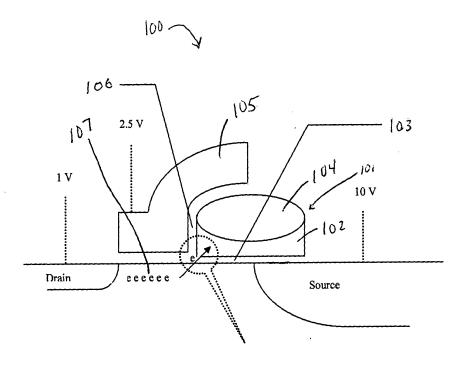
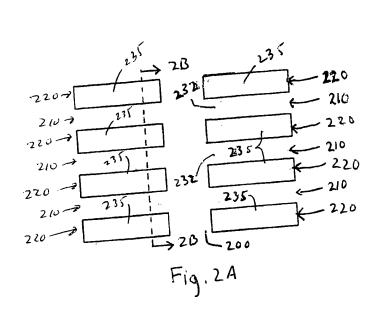


Fig.1C

Docket No. N1085-00125 Inventors: Chia-Ta Hsieh et al. "Flash Memory Cell Having Multi-Program Channels" Sheet 3 of 8



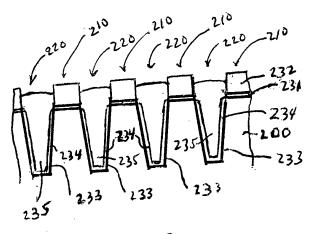


Fig. 2B

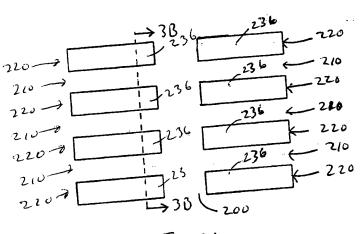


Fig. 3A

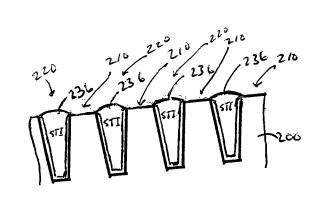
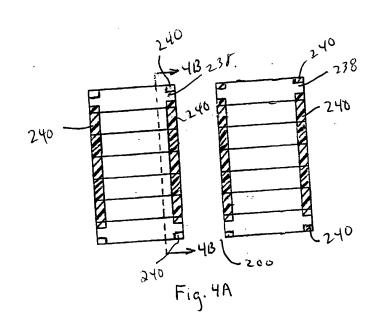


Fig. 3B



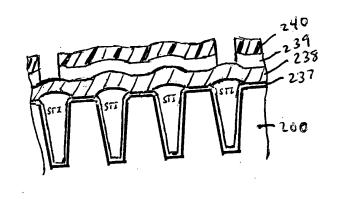
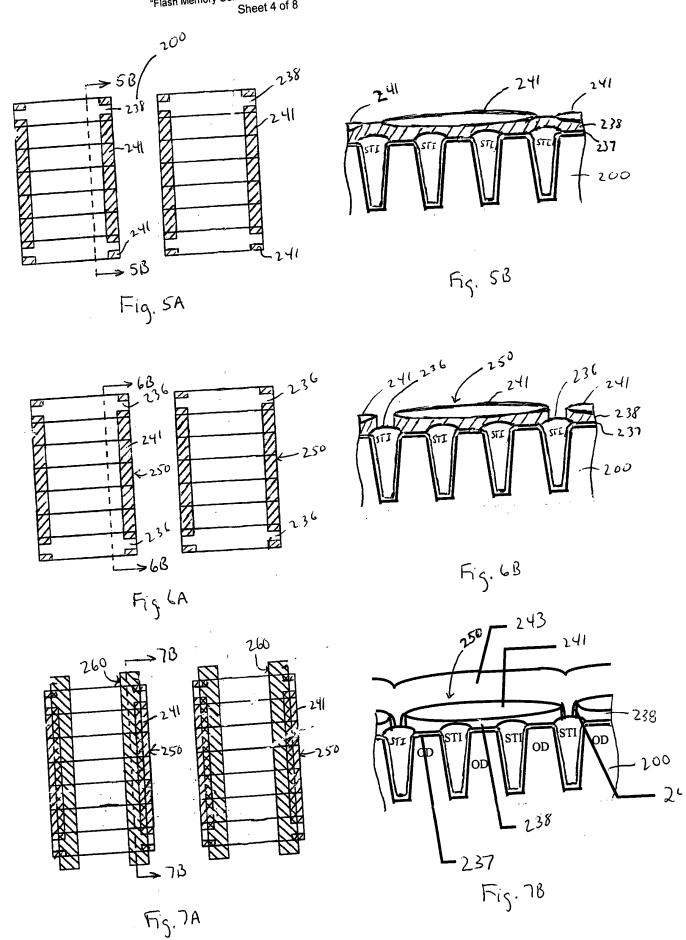
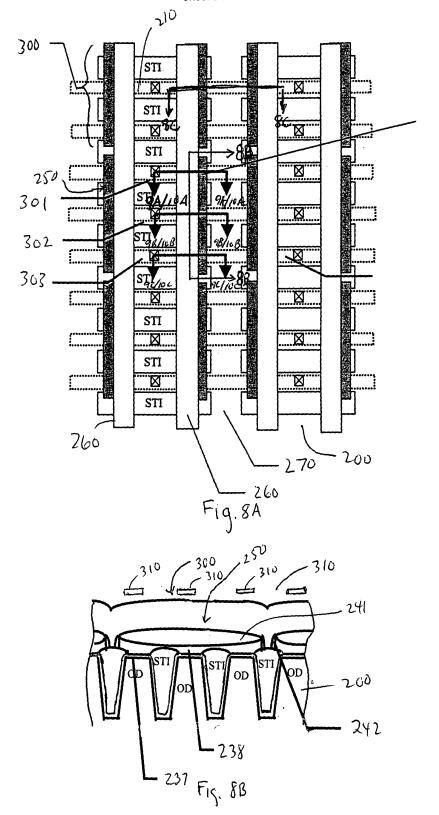


Fig. 43

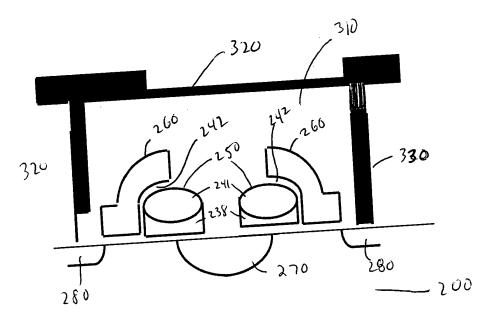
Docket No. N1085-00125 Inventors: Chia-Ta Hsieh et al. "Flash Memory Cell Having Multi-Program Channels" Sheet 4 of 8



Docket No. N1085-00125 Inventors: Chia-Ta Hsieh et al. "Flash Memory Cell Having Multi-Program Channels" Sheet 5 of 8

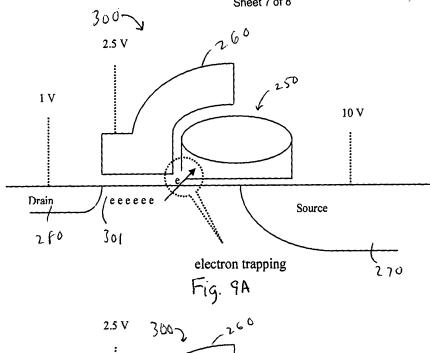


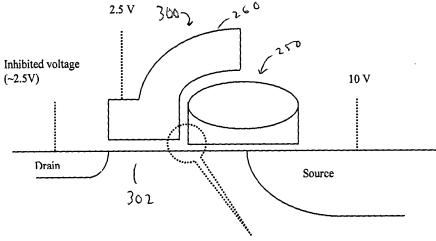
Docket No. N1085-00125
Inventors: Chia-Ta Hsieh et al.
"Flash Memory Cell Having Multi-Program Channels"
Sheet 6 of 8



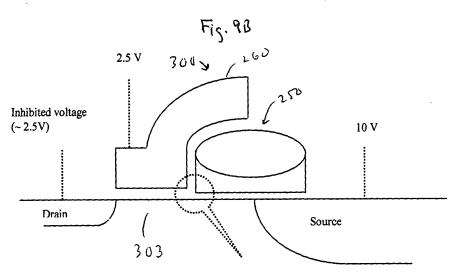
Fg. 8C

Docket No. N1085-00125 Inventors: Chia-Ta Hsieh et al. "Flash Memory Cell Having Multi-Program Channels" Sheet 7 of 8





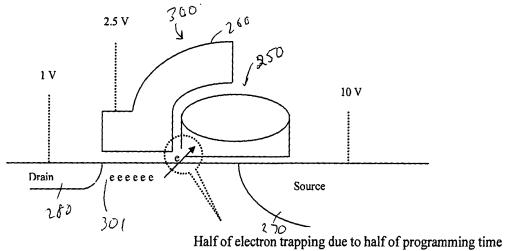
Channel turn off, so there are not electron trapping



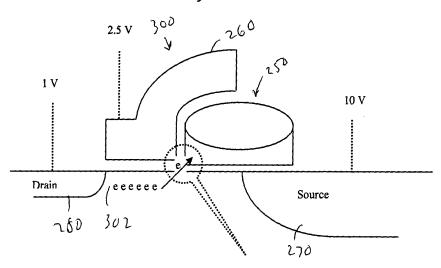
Channel turn off, so there are not electron trapping

Fig. 9C

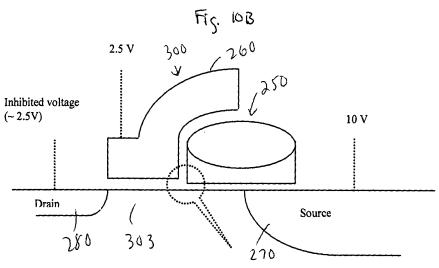
Docket No. N1085-00125 Inventors: Chia-Ta Hsieh et al. "Flash Memory Cell Having Multi-Program Channels" Sheet 8 of 8



Half of electron trapping due to half of programming time Fig. 10A



Half of electron trapping due to half of programming time



Channel turn off, so there are not electron trapping

Fig. 10L